

# isc N-Channel MOSFET Transistor

## 2SK3650-01S

### FEATURES

- Drain Current : I\_D= 33A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage : V<sub>DSS</sub>= 150V(Min)
- Static Drain-Source On-Resistance
- :  $R_{DS(on)}$  = 70m  $\Omega$  (Max) @ V<sub>GS</sub>= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

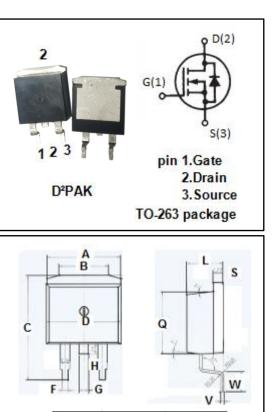
### DESCRIPTION

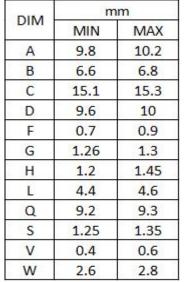
 motor drive, DC-DC converter, power switch and solenoid drive.

| SYMBOL           | PARAMETER                                   | PARAMETER VALUE       |    |
|------------------|---|-----------------------|----|
| V <sub>DSS</sub> | Drain-Source Voltage                        | in-Source Voltage 150 |    |
| V <sub>GS</sub>  | Gate-Source Voltage-Continuous              | ±30                   | V  |
| ID               | Drain Current-Continuous                    | 33                    | A  |
| I <sub>DM</sub>  | Drain Current-Single Pluse                  | 132                   | A  |
| P <sub>D</sub>   | Total Dissipation @Tc=25°C 150              |                       | W  |
| TJ               | Max. Operating Junction Temperature -55~150 |                       | °C |
| T <sub>stg</sub> | Storage Temperature -55~150                 |                       | °C |

### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | МАХ   | UNIT |
|---------------------|--------------------------------------|-------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 0.833 | °C/W |





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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS                                     | MIN | МАХ  | UNIT |
|----------------------|---------------------------------|--|-----|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA   | 150 |      | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage          | V <sub>DS</sub> = 10V; I <sub>D</sub> = 0.25mA | 3.0 | 5.0  | V    |
| R <sub>DS</sub> (on) | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 11.5A  |     | 70   | mΩ   |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0      |     | ±0.1 | uA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 150V; V <sub>GS</sub> = 0    |     | 25   | uA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 23A; V <sub>GS</sub> = 0      |     | 1.65 | V    |

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